



UNITED STATES PATENT AND TRADEMARK OFFICE  
(Case No. 211.001-D3-US)

In the Application of: **Fazan et al.**

Serial No: **10/724,648**

Filed: **December 1, 2003**

Title: **Semiconductor Device**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

) Group Art Unit:

) Before Examiner

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on March 15, 2004

Date

Michaleo Sites

(person signing this certificate)

Michaleo Sites

Signature

**FIRST INFORMATION DISCLOSURE STATEMENT**

Dear Sir:

Submitted herewith are twenty-three (23) sheets of a modified Form PTO-1449. The documents listed on the modified Form PTO-1449 were provided or cited during the prosecution of parent applications of the above-captioned application are not enclosed herewith. (See 37 C.F.R. §1.98(d) and MPEP 609). Should the Examiner desire an additional copy of the documents previously provided or cited during the prosecution of parent applications, kindly contact the undersigned.

It is respectfully requested that the Examiner make his/her consideration of these references formally of record with the initial Office Action.

Respectfully submitted,

Date: March 15, 2004

Neil A. Steinberg  
Reg. No. 34,735  
650-968-8079



PTO-1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  INFORMATION DISCLOSURE STATEMENT BY APPLICANT	ATTY. DOCKET NO. <b>211.001-D3-US</b>	SERIAL NUMBER <b>10/724,648</b>
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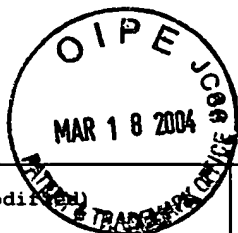
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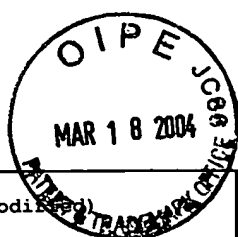
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